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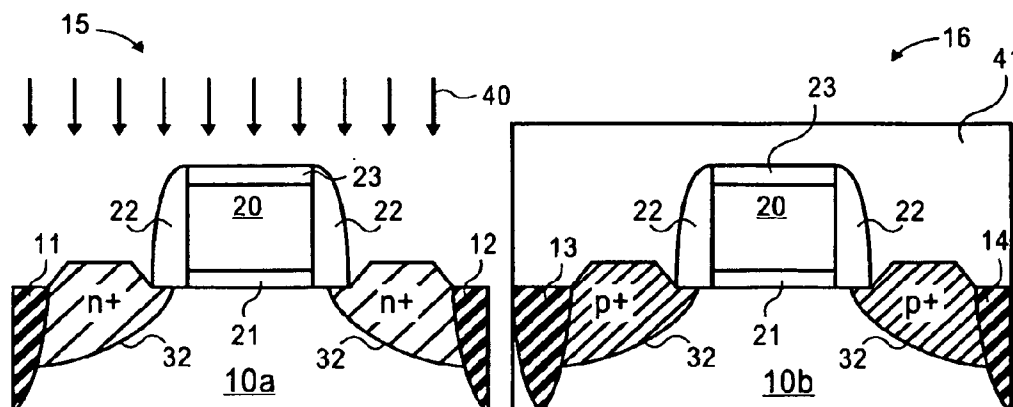
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(54) Title: EPITAXIAL SILICON GERMANIUM FOR REDUCED CONTACT RESISTANCE IN FIELD-EFFECT TRANSISTORS



(57) Abstract: A method for selectively relieving channel stress for n-channel transistors with recessed, epitaxial SiGe source and drain regions is described. This increases the electron mobility for the n-channel transistors without affecting the strain in p-channel transistors. The SiGe provides lower resistance when a silicide is formed.

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